

[NON-VOLATILE MEMORY]

Abstract of Disclosure

A non-volatile memory that combines a main memory array region and a redundant memory array region. The non-volatile memory is constructed without the use of the field oxide and dummy memories that typically separate the main and redundant memory array regions. Instead, the main memory and redundant memory are directly adjacent to each other on a doped region of the semiconductor wafer, and the bordering memory modules share a common source, drain, bit line, and ground line. A control method is used to allow the main memory decoder and redundant memory controller to pass signals and select between the main and redundant memory array areas.

10064216-052102

Figures

2025 RELEASE UNDER E.O. 14176